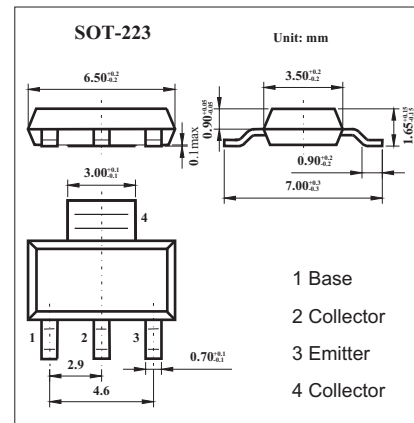


PNP High Voltage Amplifier PZTA92

Features

- High breakdown voltage
- Low collector-emitter saturation voltage
- Complementary to PZTA42(NPN)



Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-Base Voltage	V _{CB0}	-300	V
Collector-Emitter Voltage	V _{CEO}	-300	V
Emitter-Base Voltage	V _{EB0}	-5.0	V
Collector Current -Continuous	I _C	-300	mA
Collector Power Dissipation	P _C	1	W
Junction Temperature	T _j	150	°C
Storage Temperature	T _{stg}	-55 to 150	°C

Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-to-base breakdown voltage	V _{(BR)CBO}	I _C = 100 μA I _E =0	-300			V
Collector-to-emitter breakdown voltage	V _{(BR)CEO}	I _C = 1 mA I _B =0	-300			V
Emitter-to-base breakdown voltage	V _{(BR)EBO}	I _E = 100 μA I _C =0	-5.0			V
Collector cutoff current	I _{CBO}	V _{CB} = -200 V, I _E =0			-0.25	μA
Collector cutoff current	I _{EBO}	V _{CE} = -3.0V, I _C =0			-0.1	μA
DC current gain	h _{FE}	V _{CE} = -10V, I _C = -1.0mA	25			
		V _{CE} = -10V, I _C = -10mA	40			
		V _{CE} = -10V, I _C = -30mA	25			
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-20 mA, I _B = -2.0mA			-0.5	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C =-20 mA, I _B = -2.0mA			-0.9	V
Transition frequency	f _T	V _{CE} = -20V, I _C = -10mA, f=100MHz	50			MHz
Output Capacitance	C _{ob}	V _{CB} =-20V, f=1.0MHz, I _E =0			6.0	pF

Marking

Marking	A92
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